

SANYO Semiconductors DATA SHEET

An ON Semiconductor Company

N-Channel Silicon MOSFET

SCH1430 — General-Purpose Switching Device Applications

Features

- 1.8V drive
- · Halogen free compliance

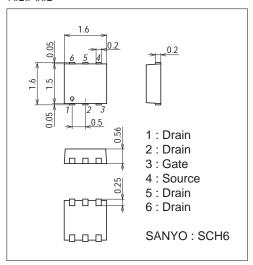
Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		20	V
Gate-to-Source Voltage	V _{GSS}		±12	V
Drain Current (DC)	ID		2	А
Drain Current (Pulse)	I _{DP}	PW≤10μs, duty cycle≤1%	8	А
Allowable Power Dissipation	PD	When mounted on ceramic substrate (900mm ² x0.8mm)	0.8	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Package Dimensions

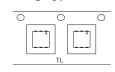
unit : mm (typ) 7028-002



Product & Package Information

Package : SCH6
 JEITA, JEDEC : SOT-563
 Minimum Packing Quantity : 5,000 pcs./reel

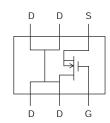
Packing Type: TL



7F

Marking

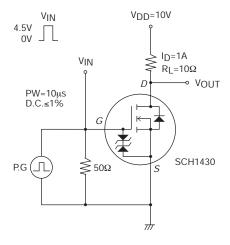
Electrical Connection

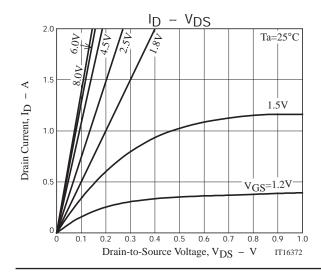


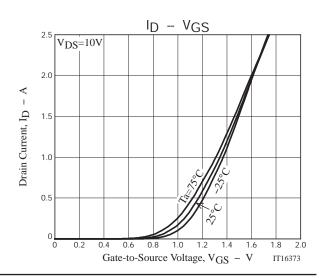
Electrical Characteristics at Ta=25°C

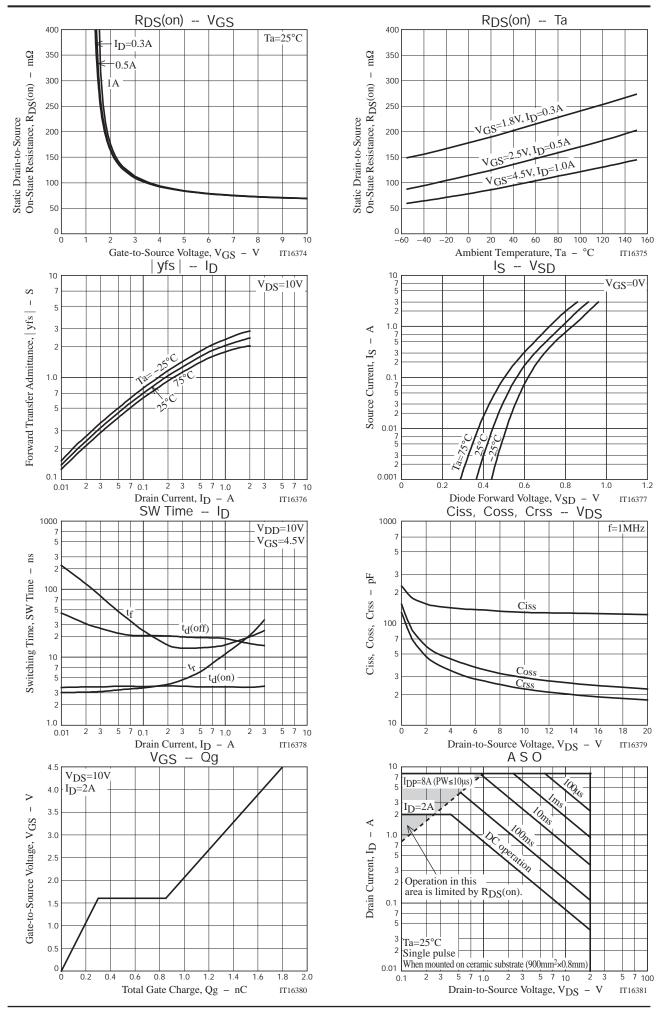
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Offic
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0V	20			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =20V, V _{GS} =0V			1	μΑ
Gate-to-Source Leakage Current	IGSS	V _{GS} =±8V, V _{DS} =0V			±10	μΑ
Cutoff Voltage	V _{GS} (off)	V _{DS} =10V, I _D =1mA	0.4		1.3	V
Forward Transfer Admittance	yfs	V _{DS} =10V, I _D =1A		1.9		S
Static Drain-to-Source On-State Resistance	R _{DS} (on)1	I _D =1A, V _{GS} =4.5V		93	125	mΩ
	R _{DS} (on)2	I _D =0.5A, V _{GS} =2.5V		135	190	mΩ
	R _{DS} (on)3	I _D =0.3A, V _{GS} =1.8V		200	310	mΩ
Input Capacitance	Ciss	V _{DS} =10V, f=1MHz		128		pF
Output Capacitance	Coss	V _{DS} =10V, f=1MHz		28		pF
Reverse Transfer Capacitance	Crss	V _{DS} =10V, f=1MHz		21		pF
Turn-ON Delay Time	t _d (on)	See specified Test Circuit.		5.1		ns
Rise Time	tr	See specified Test Circuit.		11		ns
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit.		14.5		ns
Fall Time	tf	See specified Test Circuit.		12		ns
Total Gate Charge	Qg	V _{DS} =10V, V _{GS} =4.5V, I _D =2A		1.8		nC
Gate-to-Source Charge	Qgs	V _{DS} =10V, V _{GS} =4.5V, I _D =2A		0.3		nC
Gate-to-Drain "Miller" Charge	Qgd	V _{DS} =10V, V _{GS} =4.5V, I _D =2A		0.55		nC
Diode Forward Voltage	V _{SD}	I _S =2A, V _{GS} =0V		0.85	1.2	V

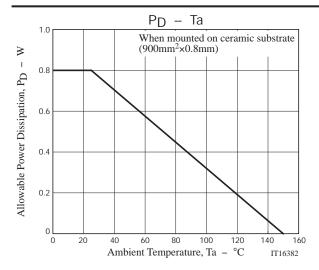
Switching Time Test Circuit











Note on usage: Since the SCH1430 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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